L Number	Hits	Search Text	DB	Time stamp
1	67	(sic or si adj c or silicon near carbide or	USPAT;	2004/08/04 09:09
1		wide near bandgap) near5 substrate and	US-PGPUB;	
ľ		(trench or trenched or groove) near6 (side	EPO; JPO;	
		or wall or sidewall or bottom) near6 (doped	DERWENT;	ļ .
		or dopant or doping or implanted or	IBM_TDB	
2	5	impurities) ("3626328" "5212104" "5488237"	USPAT	2004/08/04 08:51
2		"5977564" "6057558").PN.	USPAI	2004/08/04 08:51
7	16	(US-6693352-\$ or US-6767783-\$ or	USPAT;	2004/08/04 09:42
•	10	US-5753938-\$ or US-5747831-\$ or US-4835586-\$	US-PGPUB;	2001,00,01 03:12
		or US-6617653-\$ or US-6194741-\$ or	DERWENT	
		US-5831288-\$).did. or (US-20040079948-\$ or		[-
		US-20030127658-\$ or US-20020096687-\$ or		
		US-20030203576-\$ or US-20030178672-\$ or	}	
		US-20030227061-\$ or US-20030042538-\$).did.		
		or (US-5753938-\$).did.		2004/20/24 25 25
8	22		USPAT	2004/08/04 09:26
9 10	49	5396085.URPN. ("4571815" "4587712" "4827321"	USPAT USPAT	2004/08/04 09:32 2004/08/04 09:39
10	9	("4571815" "4587712" "4827321" "4835586" "4903189" "4961100"	USPAI	2004/08/04 09:39
		"5202750" "5233215" "5313082").PN.		
11	63	(sic or silicon adj carbide or si adj c)	USPAT;	2004/08/04 09:44
	,	near6 (sit or static adj induction adj	US-PGPUB;	2001, 00, 01 05:11
		transistor or power near2 (fet or mosfet or	DERWENT	1
		misfet or jfet)) and (trench or trenched or		1
]		groove) near4 (impurity or doped or dopant]
ļ		or doping or implant or implanted or gate or		
ļ		gated)		
- 1	336	•	USPAT;	2004/08/04 08:38
		near5 substrate and ((source or drain) near3 (back or backside or bottom) or vertical	US-PGPUB;	1
ļ		near2 channel or gate near2 trench or gated	EPO; JPO; DERWENT;	-
ļ		near2 trench or gate near2 groove)	IBM_TDB	
_	177		USPAT;	2004/08/03 15:26
		near4 substrate and gate near3 (trench or	US-PGPUB;	,,
		groove)	EPO; JPO;	
ļ			DERWENT;	•
			IBM_TDB	
	17		USPAT;	2004/08/03 15:32
		near4 substrate and gate near electrode	US-PGPUB;	
ļ		near4 (bottom or beneath or below or under or underneath or lower) near3 (trench or	EPO; JPO; DERWENT;	1
		groove)	IBM TDB	
. <u>-</u>	46		USPAT;	2004/08/03 16:01
ļ		transistor) and (sic or si adj c or silicon	US-PGPUB;	2001,00,00 10:01
	İ	near carbide) near4 substrate and (trench or	EPO; JPO;	
		groove or recess) near5 (gate or gated)	DERWENT;	
			IBM_TDB	
_	9	("4571815" "4587712" "4827321"	USPAT	2004/08/03 15:35
İ		"4835586" "4903189" "4961100"	1	
· _	_	"5202750" "5233215" "5313082").PN.	HCDam	2004/00/02 15 12
→	7	("4262296" "4941026" "4947218" "5323040" "5391895" "5396085"	USPAT	2004/08/03 15:42
ı		"5323040" "5391895" "5396085" "5506421").PN.		
, -	7	5747831.URPN.	USPAT	2004/08/03 15:44
, -	4		USPAT	2004/08/03 15:51
	أ ا	"6455364").PN.		, ,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,
	21	(jfet or sit or static adj induction adj	USPAT;	2004/08/03 16:06
		transistor) and (sic or si adj c or silicon	US-PGPUB;	
		near carbide) near4 substrate and (trench or	EPO; JPO;	
ļ		groove or recess) near3 (bottom or under or	DERWENT;	
ļ		through or beneath or underneath or below)	IBM_TDB	
	٦	near3 (doped or channel or gate or control)	HCDATT	2004/00/02 16 00
-	3	(jfet or sit or static adj induction adj transistor) and (sic or si adj c or silicon	USPAT; US-PGPUB;	2004/08/03 16:09
İ		near carbide) near4 substrate and (trench or	EPO; JPO;	
		groove or recess) near3 (bottom or under or	DERWENT;	
ł		through or beneath or underneath or below)	IBM TDB	
				1
İ		near3 (doped or doping or dopant or		

-	27	, ,	USPAT;	2004/08/03 16:14
		near4 substrate and (trench or groove or	US-PGPUB;	
		recess) near3 (bottom or under or through or	EPO; JPO;	
		beneath or underneath or below) near3 (doped	DERWENT;	
		or doping or dopant or impurity)	IBM TDB	
-	107	(sit or static adj induction adj transistor)	USPAT;	2004/08/03 16:30
		and (silicon adj carbide or sic or si adj c)	US-PGPUB;	
		near3 substrate	EPO; JPO;	!
			DERWENT;	
			IBM TDB	·
-	4	("5350699" "5859447" "6049098"	USPĀT	2004/08/03 16:18
	_	"6455364").PN.		
_	6		USPAT	2004/08/03 16:19
		"5262669" "5753960" "6097046").PN.		
_	2		USPAT	2004/08/03 16:25
-		(jfet) and (silicon adj carbide or sic or si	USPAT;	2004/08/03 16:31
		adj c) near3 substrate	US-PGPUB;	=====================================
		, and and and and and and and and and and	EPO; JPO;	
			DERWENT;	
			IBM TDB	
_	64	(jfet) and (silicon adj carbide or sic or si	USPAT;	2004/08/03 16:31
		adj c) near3 substrate and (trench or groove	US-PGPUB;	2001,00,03 10.31
		or trenched)	EPO; JPO;	
		or cremenca,	DERWENT;	
			IBM TDB	
l _	72	(jfet) and (silicon adj carbide or sic or si	USPAT;	2004/08/03 16:35
	1	adj c) near3 substrate and (trench or groove	US-PGPUB;	2004/00/03 10:33
		or trenched or recess or recessed)	EPO; JPO;	
		or cremencu or recess or recessed,	DERWENT;	′
			IBM TDB	
1_	353	(jfet or sit or static adj induction adj	USPAT;	2004/08/03 16:37
	, ,,,,	transistor) and (gan or gap or cds or zno or	US-PGPUB;	2004/00/03 10:3/
		zns or gallium adj nitride or gallium adj	EPO; JPO;	
		phosphide or cadmium adj sulfide or zinc adj	DERWENT;	
		oxide or zinc adj sulfide or (high or large)	IBM TDB	
		near2 (bandgap or gap)) near3 substrate	1 101 100	
_	24	(jfet or sit or static adj induction adj	USPAT;	2004/08/03 16:38
	24	transistor) and (gan or gap or cds or zno or	US-PGPUB;	2004/00/03 16:38
		zns or gallium adj nitride or gallium adj	EPO; JPO;	
		phosphide or cadmium adj sulfide or zinc adj	DERWENT;	
		oxide or zinc adj sulfide or (high or large)		
		near2 (bandgap or gap)) near3 substrate and	IBM_TDB	
		(trench or trenched or groove or recess or		
		recessed) near3 (gate or channel or control		
L		or impurity or dopant or doped or doping)	L	1

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